

PH100-SIUV-OD1-D0

Photodiode detector for laser power measurement up to 38 mW.



PRODUCT FAMILY KEY FEATURES

LARGE APERTURES

10 mm \emptyset for the silicon sensors

3 VERSIONS

- Silicon 350 1080 nm, up to 750 mW
- Silicon-UV 210 1080 nm, up to 38 mW
- Germanium 800 1650 nm, up to 500 mW

CHOICE OF ATTENUATORS

Models with attenuators include a calibration both with and without the removable filter

HIGH ACCURACY

The new PH100-SI-HA presents the lowest calibration uncertainty to date.

13.7 mm

202790

PRECISE CALIBRATION

Wavelength selection in 1 nm steps

SMART INTERFACE

Containing all the calibration data

COMPATIBLE STAND

STAND-D-233

SPECIFICATIONS

Maximum average power ¹	38 mW
Noise equivalent power ²	200 pW
Spectral range	400 - 1080 nm
Typical rise time	0.2 s
Power calibration uncertainty ³	±5.0 % (400 - 1009 nm) ±7.5 % (1010 - 1080 nm)
Peak sensitivity	850 nm
Minimum repetition rate ⁴	155 kHz
At 532 nm, with attenuator. See curves for maximum power at other wavelengths. At 850 nm. Nominal value. Actual value depends on environmental electromagnetic interference and wavelength.	

- 3. With attenuator. See user manual for calibration uncertainty without attenuator.
- 4. See user manual for details.

DAM	IAGE	THRES	HOLDS

100 W/cm² Maximum average power density

PHYSICAL CHARACTERISTICS

Aperture diameter	10 mm
Absorber	SiUV
Dimensions	38.1Ø x 36D mm
Weight	0.14 kg

ORDERING INFORMATION

Distance to sensor face

PH100-SiUV-OD1-INT-D0

PH100-SiUV-OD1-D0	200881
PH100-SiUV-OD1-IDR-D0	203234

Specifications are subject to change without notice. Refer to the user manual for complete specifications.

INTERESTED IN THIS PRODUCT?

GET A QUOTE

Find your local sales representative at gentec-eo.com/contact-us